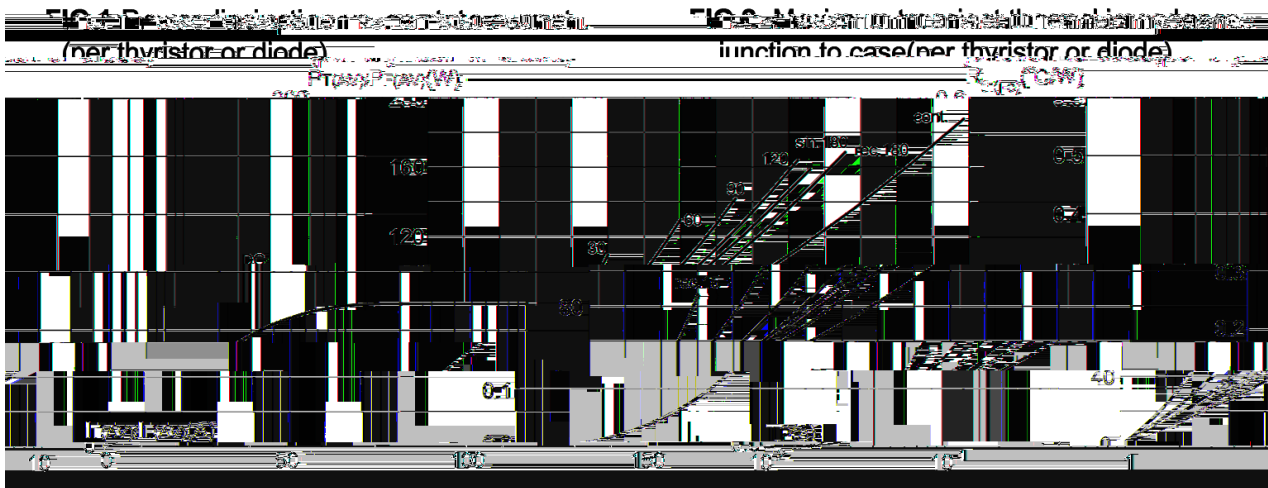






	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					



G.3: Forward characteristics
(per thyristor or diode)

A) $I_T(A)$

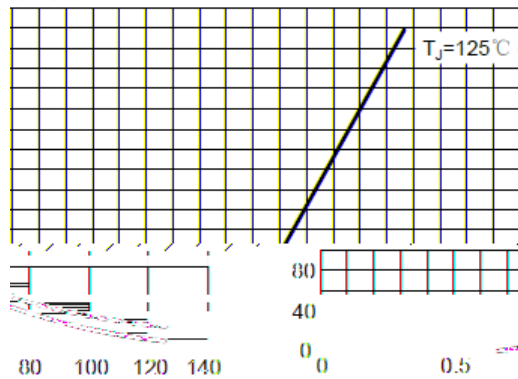
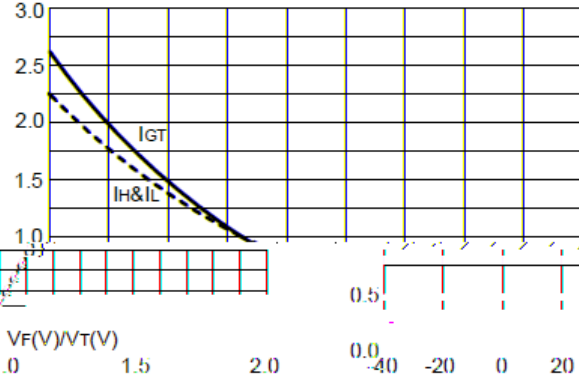


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

$I_{GT, IH, IL}(T_J)/I_{GT, IH, IL}(T_J=25°C)$



FI

$I_F(A)$

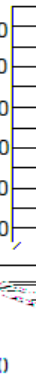


FIG.5: Gate trigger characteristics

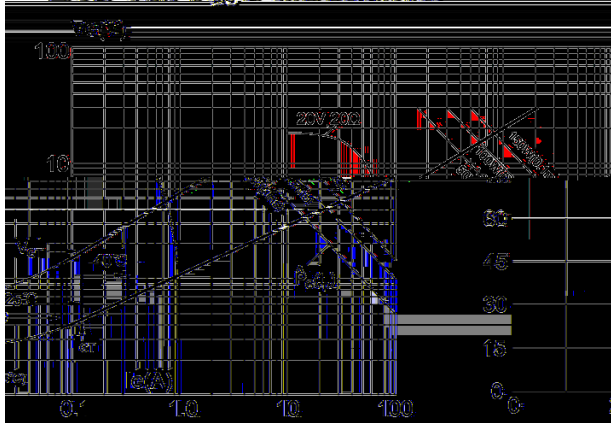


FIG.6: Forward current vs. case temperature

